

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

SOT-23 Plastic-Encapsulate Transistors

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR

S9013 TRANSISTOR (NPN)

FEATURES

- **Complementary to S9012**
- **Excellent h_{FE} linearity**

MARKING: J3

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Power Dissipation	300	mW
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 0.1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=20V, I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C= 50mA	120		400	
	$h_{FE(2)}$	V_{CE}=1V, I_C=500mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500mA, I_B= 50mA			0.6	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500mA, I_B= 50mA			1.2	V
Transition frequency	f_T	V_{CE}=6V, I_C= 20mA f=30MHz	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400

Typical Characteristics

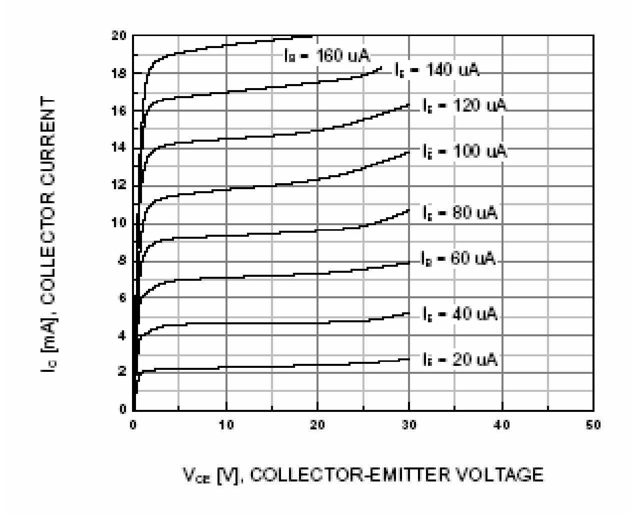


Figure 1. Static Characteristic

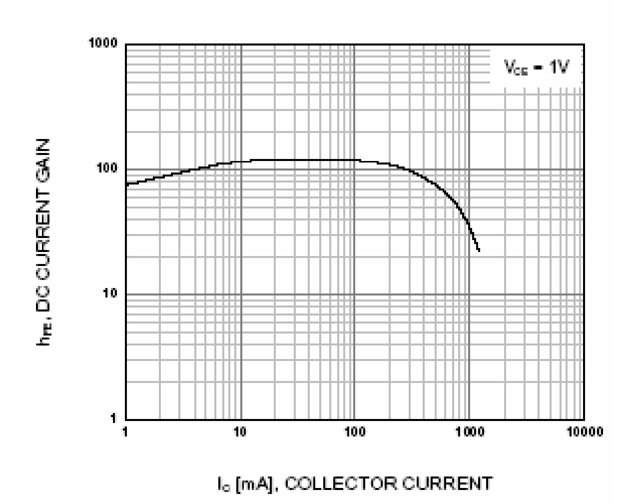


Figure 2. DC current Gain

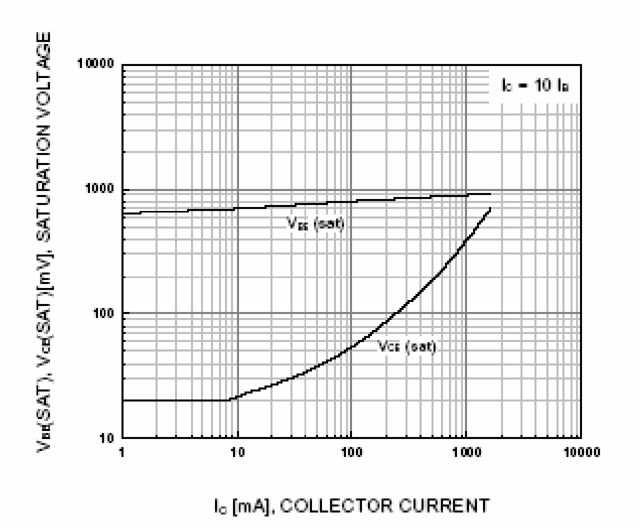


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

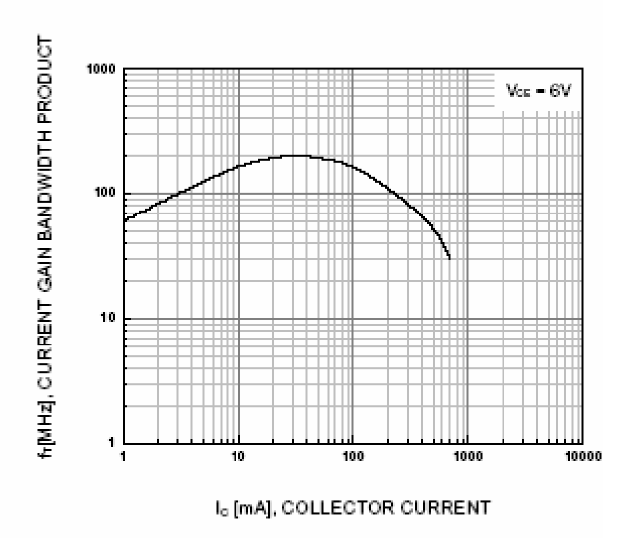


Figure 4. Current Gain Bandwidth Product